#### TOSHIBA BI-DIRECTIONAL TRIODE THYRISTOR SILICON PLANAR TYPE

# SM2LZ47

#### AC POWER CONTROL APPLICATIONS

• Repetitive Peak Off–State Voltage:  $V_{DRM} = 800V$ 

• R.M.S. On-State Current: IT (RMS) = 2A

• High Commutation (dv / dt): (dv / dt)  $c = 5V / \mu s$  (Min.)

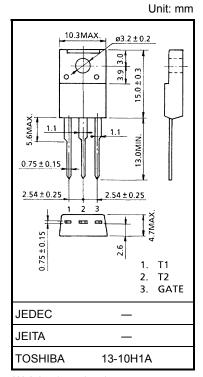
• Isolation Voltage: VISOL = 1500V AC

#### **MAXIMUM RATINGS**

CHARACTERISTIC	SYMBOL	RATING	UNIT		
Repetitive Peak Off-State Voltage	$V_{DRM}$	800	V		
R.M.S. On-State Current (Full Sine Waveform)	I <sub>T (RMS)</sub>	2	Α		
Peak One Cycle Surge On-State	l-o.	8 (50Hz)	А		
Current (Non-Repetitive)	ITSM	8.8 (60Hz)			
I <sup>2</sup> t Limit Value	I <sup>2</sup> t	0.32	A <sup>2</sup> s		
Critical Rate of Rise of On-State Current (Note)	di / dt	50	A / µs		
Peak Gate Power Dissipation	$P_{GM}$	3	W		
Average Gate Power Dissipation	P <sub>G (AV)</sub>	0.3	W		
Peak Gate Voltage	$V_{FGM}$	10	V		
Peak Gate Current	I <sub>GM</sub>	1.6	Α		
Junction Temperature	Tj	-40~125	°C		
Storage Temperature Range	T <sub>stg</sub>	-40~125	°C		
Isolation Voltage (AC, t = 1min.)	V <sub>ISOL</sub>	1500	V		

Note: di / dt test condition

 $V_{DRM}$  = 400V,  $I_{TM} \le 3A$ ,  $t_{gw} \ge 10\mu s$ ,  $t_{gr} \le 250ns$ ,  $i_{gp} = I_{GT} \times 2.0$ 

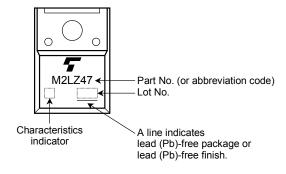


Weight: 1.7 g (typ.)

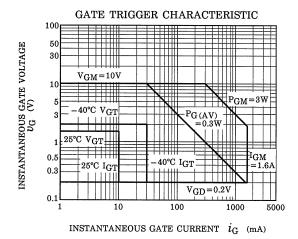
## ELECTRICAL CHARACTERISTICS (Ta = 25°C)

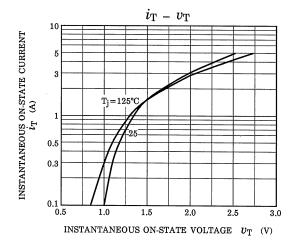
CHARACTERISTIC	CHARACTERISTIC SYMBOL TEST CONDITION		MIN	TYP.	MAX	UNIT		
Repetitive Peak Off-State Current I <sub>DRM</sub> V <sub>DRM</sub> = 800V		_	_	20	μΑ			
Gate Trigger Voltage	I	V <sub>GT</sub>	V <sub>D</sub> = 12V, R <sub>L</sub> = 20Ω	T2 (+) , Gate (+)	_	_	1.5	٧
	II			T2 (+), Gate (-)	_	_	1.5	
	III			T2 (-) , Gate (-)	_	_	1.5	
Gate Trigger Current	I	I <sub>GT</sub>	V <sub>D</sub> = 12V, R <sub>L</sub> = 20Ω	T2 (+), Gate (+)	_	_	10	mA
	II			T2 (+) , Gate (-)	_	_	10	
	III			T2 (-) , Gate (-)	_	_	10	
Peak On-State Voltage		V <sub>TM</sub>	I <sub>TM</sub> = 3A		_	_	2.0	V
Gate Non-Trigger Voltage		$V_{GD}$	V <sub>D</sub> = 800V, Tc = 125°C		0.2	_	_	V
Holding Current		lΗ	V <sub>D</sub> = 12V, I <sub>TM</sub> = 1A		_	_	10	mA
Thermal Resistance		R <sub>th (j-a)</sub>	Junction to Ambient, AC		_	_	58	°C/W
Critical Rate of Rise of Off-State Voltage d		dv / dt	V <sub>DRM</sub> = 800V, T <sub>j</sub> = 125°C Exponential Rise		_	500	_	V / µs
Critical Rate of Rise of Off-State Voltage at Communication		(dv / dt) c	$V_{DRM}$ = 400V, $T_j$ = 125°C (di / dt) c = - 0.5A / ms		5	_	_	V / µs

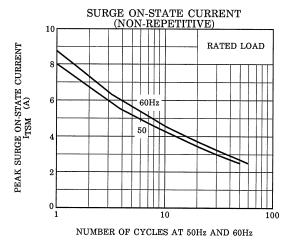
### **MARKING**

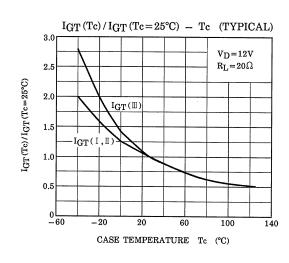


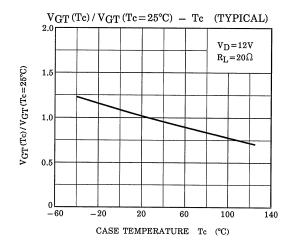
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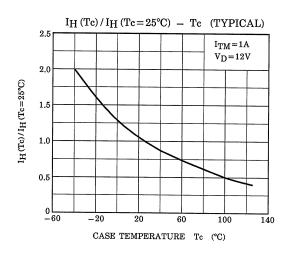


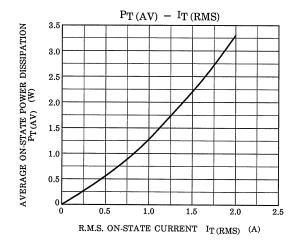


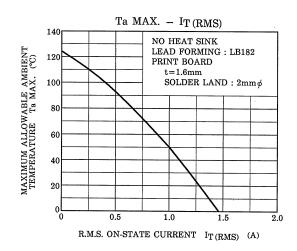


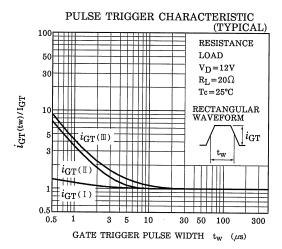


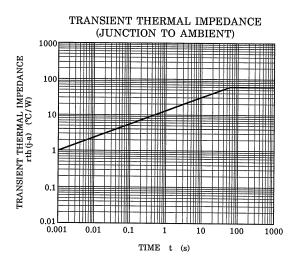












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5 2004-07-06